

IN THE SPECIFICATION

Please substitute the following paragraph for the paragraph starting at page 4, line 1 and ending at line 11. A marked-up copy of this paragraph, showing the changes made thereto is attached.

B<sup>1</sup>  
--In the case of the electron beam projection apparatus described above, the exposure width of one exposure operation is generally several mm to several ten mm. Image distortion and off-axis aberration mainly caused by field curvature of the projection lens become larger than in the conventional apparatus, thus degrading the exposure pattern's resolution. In order to prevent degradation in the resolution, the region of the pattern of the mask to be irradiated with the electron beam may be reduced. However, this cannot achieve a great improvement in productivity as compared to the conventional electron beam exposure method.--

Please substitute the following paragraph for the paragraph starting at page 16 , line 11 and ending at line 18. A marked-up copy of this paragraph, showing the changes made thereto is attached.

B<sup>2</sup>  
--The charged particle projection system of this embodiment has a charged particle beam source 1, a reduction lens 3, a charged particle shaping aperture 4, a collimator lens 6, and first and second projection lenses 9 and 11. A charged particle beam 2 emerging from the charged particle beam source 1 irradiates a mask 7 placed on a mask stage 8 to transfer a pattern on the mask 7 onto a sample 12 on sample stage 13.--